

AMENDMENTS TO THE CLAIMS

1-10. (Canceled)

11. (Currently Amended): A method for manufacturing a reflective liquid crystal display device, the method comprising:

a plurality of gate lines and data lines on a first substrate, the gate lines crossing the data lines;

forming a thin film transistor near the crossing ~~on the intersection~~ of the gate line and the data line, the thin film transistor including a gate electrode, a semiconductor layer, a source electrode and a drain electrode;

forming a capacitor lower electrode of a storage capacitor on the same plane as the gate line;

forming an insulation film on the capacitor lower electrode;

forming an capacitor upper electrode on an upper portion of the capacitor lower electrode, the capacitor upper electrode being formed integrally with the drain electrode; [[and]]

forming a passivation layer on the capacitor upper electrode; and

forming a reflective electrode on the passivation layer, the reflected electrode being electrically connected with the drain electrode.

12. (Currently Amended): A method for manufacturing a transfective liquid crystal display device, which has pixel areas defined into a reflection part and a transmission part, the method comprising:

forming intersecting a plurality of gate lines and data lines on a first substrate, the gate lines crossing the data lines;

forming a thin film transistor near the crossing ~~on the intersection~~ of the gate line and the data line, the thin film transistor including a gate electrode, a semiconductor layer, a source electrode and a drain electrode;

forming a capacitor lower electrode of a storage capacitor on the same plane as the gate line;

forming an insulation film on the capacitor lower electrode;

forming a capacitor upper electrode on an upper portion of the capacitor lower electrode, the capacitor upper electrode being formed integrally with the drain electrode;

forming a passivation layer on the capacitor upper electrode;

forming a reflective electrode on the passivation layer, the reflective electrode electrically connected with the drain electrode at the reflection area; and

forming a transfective electrode connected with the reflective electrode at the transmission area.

13. (Previously Presented): The method for manufacturing of claim 11, wherein the insulation film is formed of one of silicone nitride (SiN_x) and silicone oxide (SiO_x).

14. (Currently Amended): A method for manufacturing a reflective liquid crystal display device, comprising:

intersecting a plurality of gate lines and data lines on a first substrate;

forming a thin film transistor on the intersection of the gate line and the data line, the thin film transistor including a gate electrode, a semiconductor layer, a source electrode and a drain electrode;

forming a capacitor lower electrode of a storage capacitor on the same plane as the gate line;

forming an insulation film on the capacitor lower electrode;

forming an capacitor upper electrode on an upper portion of the capacitor lower electrode, the capacitor upper electrode being formed integrally with the drain electrode;

forming a reflective electrode connected with the drain electrode; and ~~The method for manufacturing of claim 11, further comprising~~

forming a passivation layer between the capacitor upper electrode and the reflective electrode.

15. (Previously Presented): The method for manufacturing of claim 14, wherein the passivation layer is one of silicone nitride (SiN_x), BCB and acryl resin.

16. (Previously Presented): The method for manufacturing of claim 12, wherein the capacitor upper electrode extends along a boundary part between the reflective electrode and the transmissive electrode to prevent light leakage.

17. (Currently Amended): The method for manufacturing of claim 12, wherein the insulation film is formed of one of silicone nitride (SiNx) and silicone oxide (SiOx).

18. (Currently Amended): A method for manufacturing a transfective liquid crystal display device, which has pixel areas defined into a reflection part and a transmission part, the method comprising:

intersecting a plurality of gate lines and data lines on a first substrate;

forming a thin film transistor on the intersection of the gate line and the data line, the thin film transistor including a gate electrode, a semiconductor layer, a source electrode and a drain electrode;

forming a capacitor lower electrode of a storage capacitor on the same plane as the gate line;

forming an insulation film on the capacitor lower electrode;

forming a capacitor upper electrode on an upper portion of the capacitor lower electrode, the capacitor upper electrode being formed integrally with the drain electrode;

forming a reflective electrode connected with the drain electrode at the reflection area;

forming a transfective electrode connected with the reflective electrode at the transmission area; and ~~The method for manufacturing of claim 12, further comprising~~

~~forming a passivation layer between the capacitor upper electrode and the reflective electrode.~~

19. (Previously Presented): The method for manufacturing of claim 18, wherein the passivation layer is one of silicone nitride (SiNx), BCB and acryl resin.

20. (Currently Amended): The method for manufacturing of claim 12, further comprising forming [[a]] another insulation layer between the reflective electrode and the transmissive electrode.

21. (New): The method for manufacturing of claim 14, wherein the insulation film is formed of one of silicone nitride (SiN_x) and silicone oxide (SiO_x).
22. (New): The method for manufacturing of claim 11, wherein the passivation layer is one of silicone nitride (SiN_x), BCB and acryl resin.
23. (New): The method for manufacturing of claim 18, wherein the capacitor upper electrode extends along a boundary part between the reflective electrode and the transmissive electrode to prevent light leakage.
24. (New): The method for manufacturing of claim 18, wherein the insulation film is formed of one of silicone nitride (SiN_x) and silicone oxide (SiO_x).
25. (New): The method for manufacturing of claim 12, wherein the passivation layer is one of silicone nitride (SiN_x), BCB and acryl resin.
26. (New): The method for manufacturing of claim 18, further comprising forming another insulation layer between the reflective electrode and the transmissive electrode.